

7th IEEE Electron Devices Technology and Manufacturing (EDTM) Conference 2023

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27G. High Voltag	e Compact Modeling	
Session Date:	March 8(Wed.), 2023	
Session Time:	17:00-18:25	
Session Room:	Room G (#318)	
Session Chair	Prof. Jongwook Jeon (Konkuk University)	
[27G-1] [Invited]		17:00-17:25
Deep-Learning Based Parameter Extraction of Device Models		
Sourabh Khandelwa	al and Fredo Chavez	
Macquarie Universi	ity	
[27G-2]		17:25-17:40
An Improved Robust Infinitely Differentiable Drift Resistance Model for BSIM High Voltage		
Compact Model		
Anant Singhal ¹ , Garima Gill ¹ , Girish Pahwa ² , Chenming Hu ² and Harshit Agarwal ¹		
¹ Indian Institute of	Technology Jodhpur, ² University of California	
[27G-3] 17:40-		17:40-17:55
A New Back-To-Back Graded AlGaN Barrier for Complementary Integration Technique Based		
	ack Graded Algary barrier for complementary integration re	chnique Based
on GaN/AlGaN/Ga		chnique Based
on GaN/AlGaN/Ga		chnique Based
on GaN/AlGaN/Ga Jinggui Zhou ¹ , Huy	N Platform	
on GaN/AlGaN/Ga Jinggui Zhou ¹ , Huy	-Binh Do ² and Maria Merlyne De Souza ¹	
on GaN/AlGaN/Ga Jinggui Zhou ¹ , Huy ¹ The University of . [27G-4]	-Binh Do ² and Maria Merlyne De Souza ¹	ation 17:55-18:10
on GaN/AlGaN/Ga Jinggui Zhou ¹ , Huy ¹ The University of 3 [27G-4] Characterization a	IN Platform -Binh Do ² and Maria Merlyne De Souza ¹ Sheffield, ² Ho Chi Minh City University of Technology and Educa	ation 17:55-18:10 r MOSFETs
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